

Fig. 1

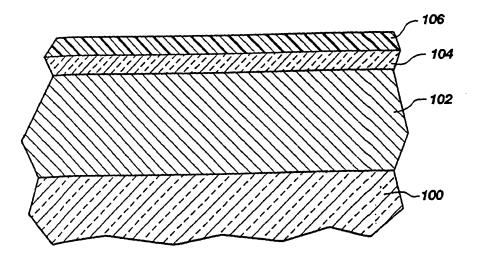


Fig. 2

SEMICONDUCTOR MEMORY DEVICE AND METHODS OF FABRICATING THE SAME
Inventor: Doan et al.
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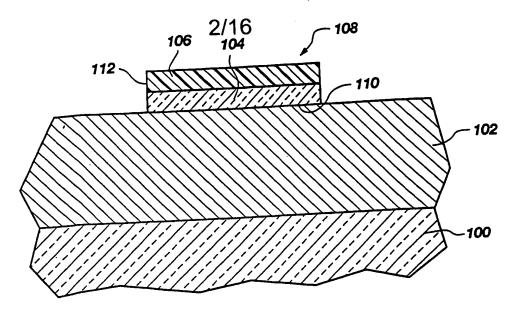


Fig. 3

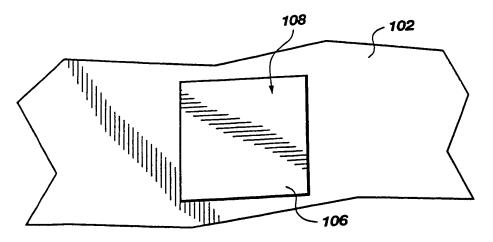


Fig. 4a

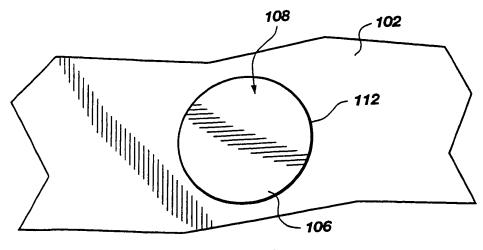


Fig. 4b

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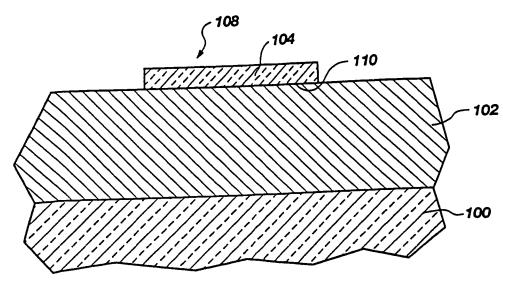


Fig. 5

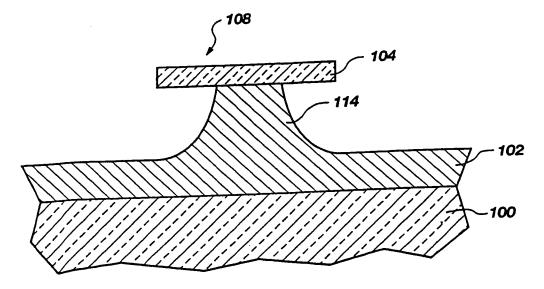


Fig. 6

TITLE: CONTROLLABLE OVUNIC FAISS-CONTROLLABLE OVUNIC FAISS-CONTROLLABL

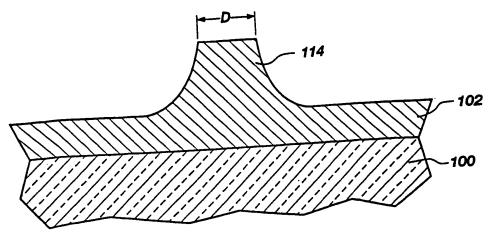


Fig. 7

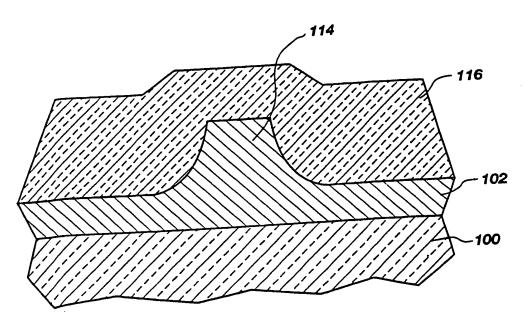
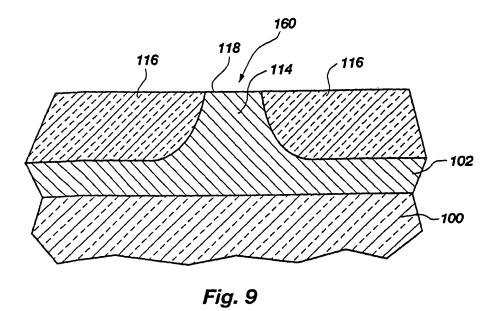
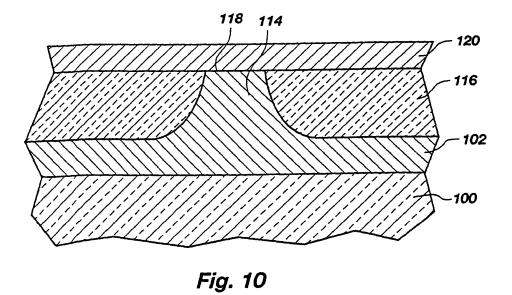


Fig. 8

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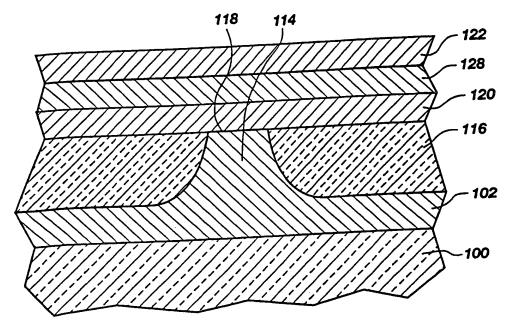


Fig. 11

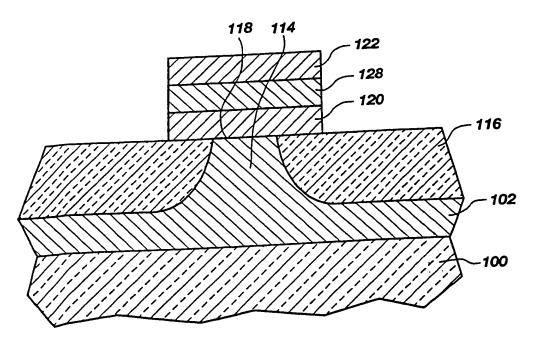


Fig. 12

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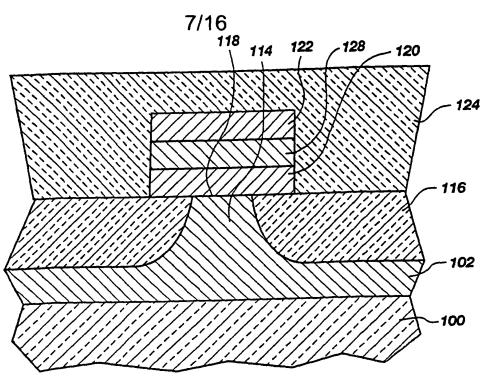


Fig. 13

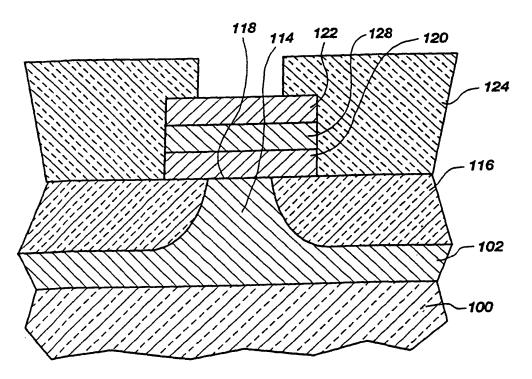
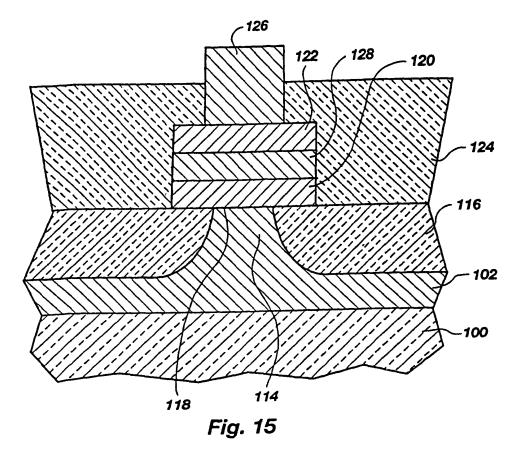


Fig. 14

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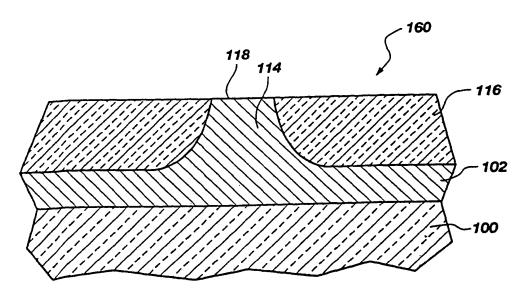


Fig. 16

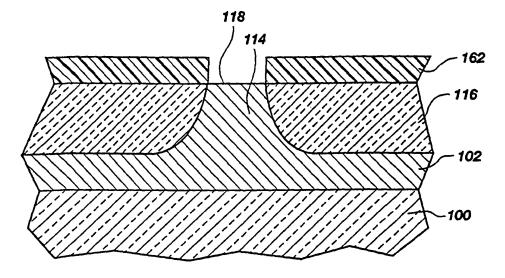
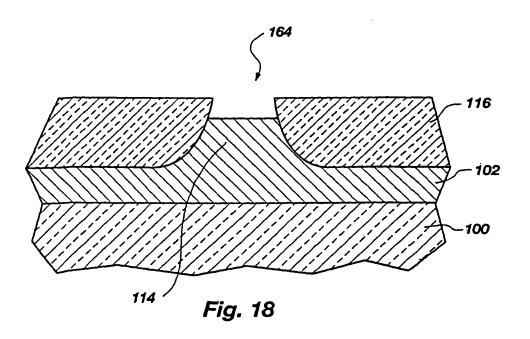
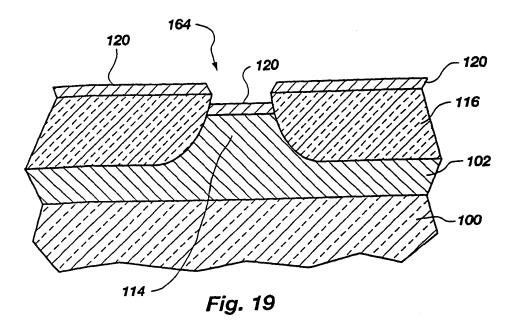
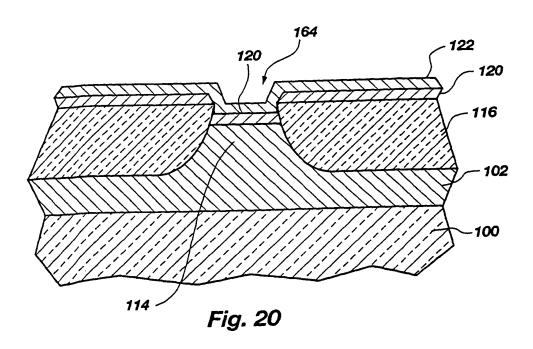


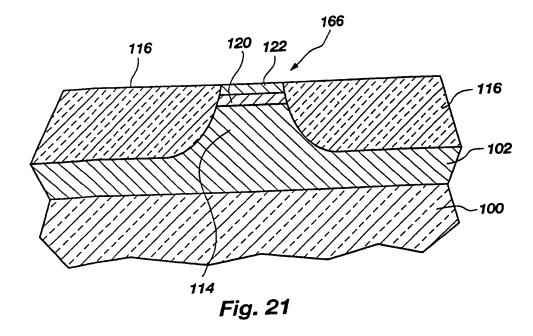
Fig. 17







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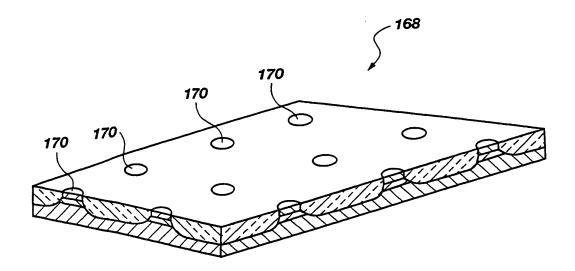


Fig. 22

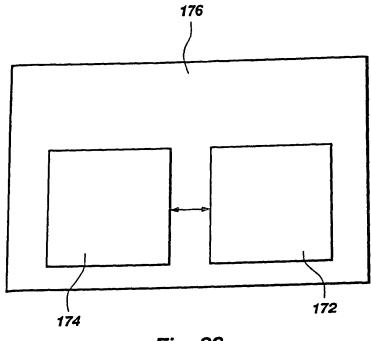


Fig. 23

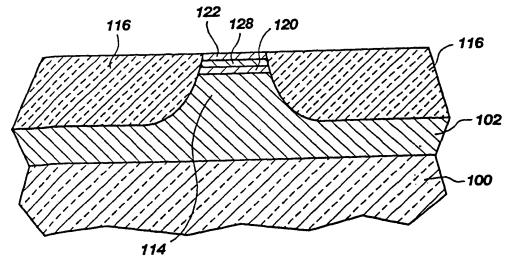


Fig. 24

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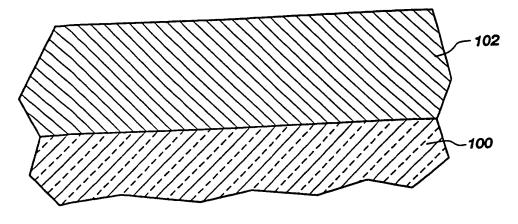


Fig. 25

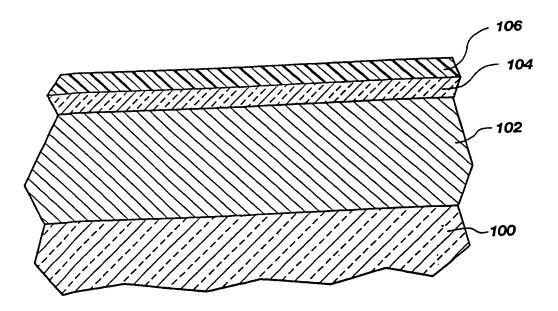


Fig. 26

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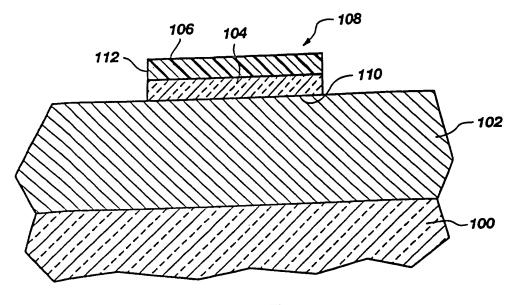


Fig. 27

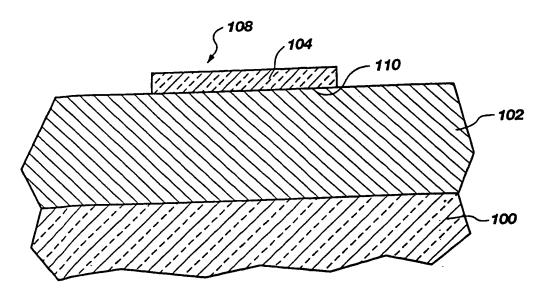


Fig. 28

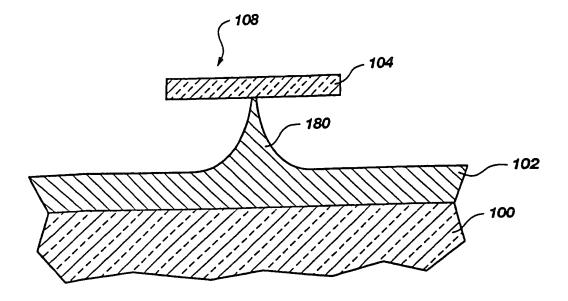


Fig. 29

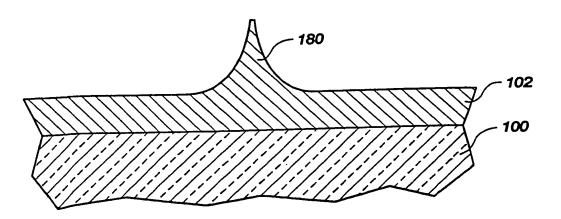
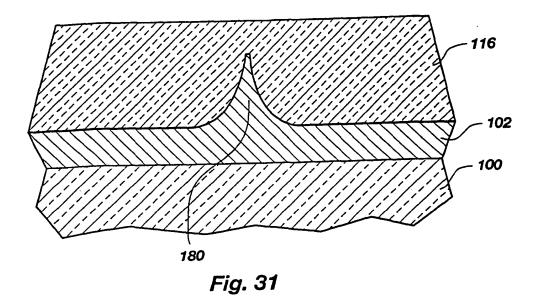


Fig. 30

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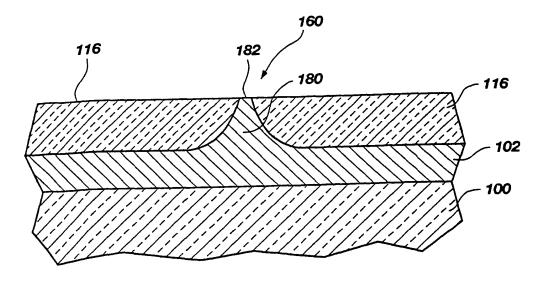


Fig. 32